Document Number: ITGH09150C6 Preliminary Datasheet V1.0

## 40W,12.5V High Power RF LDMOS FETs

### **Description**

The ITGH09150C6 is a 40-watt, highly rugged, unmatched LDMOS FET, designed for commercial and industrial applications at frequencies up to 520MHz. It can be used in linear or saturated power amplifier, for CW and pulsed signal, and any modulation format. It is also featured by its lower cost of plastic open cavity for surface mount on PCB through vias

### ITGH09150C6



Typical UHF CW Performance (On Innogration fixture with device soldered). Vds=12.5V, Idq=20mA

Freq	P1dB	P1dB	P1dB	P1dB	P3dB	P3dB	P3dB
(MHz)	(dBm)	(W)	Eff(%)	Gain(dB)	(dBm)	(W)	Eff(%)
520	45. 75	37.6	65.6	21. 37	46.5	44.6	68

#### **Features**

- High Efficiency and Linear Gain Operations
- Integrated ESD Protection
- Excellent thermal stability, low HCl drift
- Large Positive and Negative Gate/Source Voltage Range for Improved Class C Operation
- Pb-free, RoHS-compliant

### **Suitable Applications**

- HF to UHF Land mobile radio (LMR)
- · ISM applications

#### **Table 1. Maximum Ratings**

Rating	Symbol	Value	Unit
DrainSource Voltage	V <sub>DSS</sub>	+65	Vdc
GateSource Voltage	$V_{GS}$	-10 to +10	Vdc
Operating Voltage	$V_{DD}$	+24	Vdc
Storage Temperature Range	Tstg	-65 to +150	°C
Case Operating Temperature	T <sub>c</sub>	+150	°C
Operating Junction Temperature	ΤJ	+225	°C

#### **Table 2. Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case	Do 10	0.5	°C/W
T <sub>C</sub> = 85°C, T <sub>J</sub> =200°C, DC test	Rejc	0.5	-0/00

#### **Table 3. ESD Protection Characteristics**

Test Methodology	Class
Human Body Model (per JESD22A114)	Class 2

#### Table 4. Electrical Characteristics (TA = 25 °C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
DC Characteristics	•		•	•	~
Drain-Source Voltage	V		0.5		
V <sub>GS</sub> =0, I <sub>DS</sub> =100uA	V <sub>(BR)DSS</sub>		65		V
Zero Gate Voltage Drain Leakage Current	I <sub>DSS</sub>			1	μА



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(V <sub>DS</sub> = 13.6V, V <sub>GS</sub> = 0 V)				
GateSource Leakage Current		 	1	
$(V_{GS} = 9 \text{ V}, V_{DS} = 0 \text{ V})$	I <sub>GSS</sub>		I	μΑ
Gate Threshold Voltage	V (45)	 2		V
$(V_{DS} = 13.6V, I_D = 600 \mu A)$	V <sub>GS</sub> (th)	2		V
Gate Quiescent Voltage	V	 2.86		V
(V <sub>DD</sub> = 13.6V, I <sub>D</sub> = 100mA, Measured in Functional Test)	$V_{GS(Q)}$	 2.00		V

 $\textbf{Load Mismatch (In Innogration Test Fixture, 50 ohm system):} \quad V_{DD} = 13.6 \text{Vdc}, \ I_{DQ} = 10 \text{ mA}, \ f = 520 \text{ MHz}$ 

VSWR 10:1 at 40W pulse CW Output Power	No Device Degradation

Figure 1:Pin Definition(Top View)



Pin No.	Symbol	Description
1-7,12,13,18-25,30,31,36	GND	DC/RF Ground
8,9,10,11,14,15,16,17	Vgs/RF In	Vgs and RF input
26,27,28,29,32,33,34,35	Vds/RF out	Vds and RF output
Package Base	GND	DC/RF Ground.



# Reference Circuit of Test Fixture Assembly Diagram 520MHz RO4350B 20mils

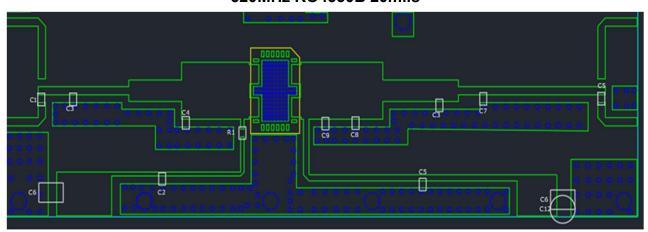


Figure 5. Test Circuit Component Layout

**Table 5. Test Circuit Component Designations and Values** 

Component	Value	Quantity
C1	3.9pF	1
C2	220pF	1
R1	10 ohm	1
C3	20pF	2
C4	8.2pF	1
C5	100pF	2
C6	10uF	2
C7	10pF	1
C8	6.8pF	1
С9	18pF	1
C12	470uF	1



Figure 1: Network analyzer Output S21/S11

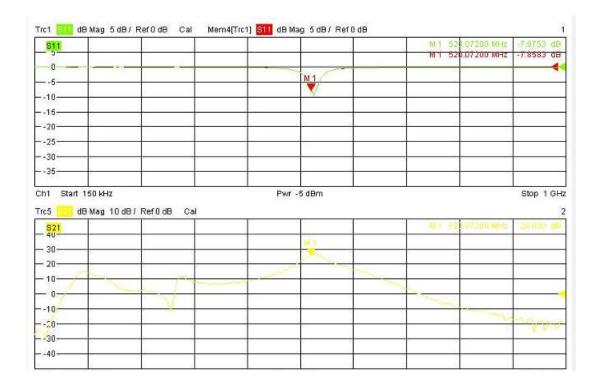
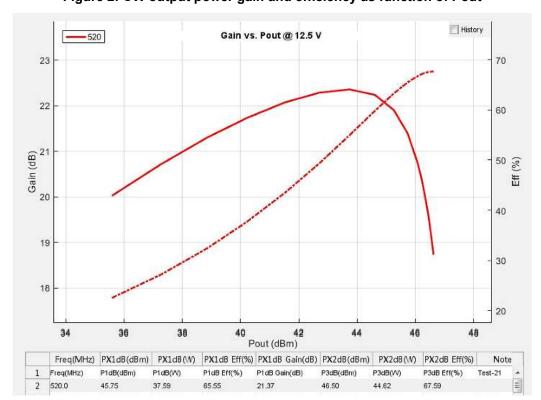
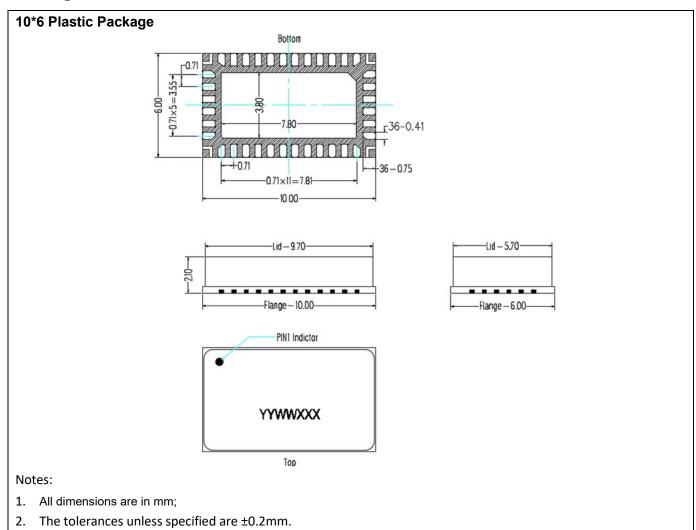


Figure 2: CW output power gain and efficiency as function of Pout



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### **Package Dimensions**



#### **Revision history**

Table 7. Document revision history

Date	Revision	Datasheet Status
2024/6/24	Rev 1.0	Preliminary Datasheet

### Application data based on ZXY-24-20

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